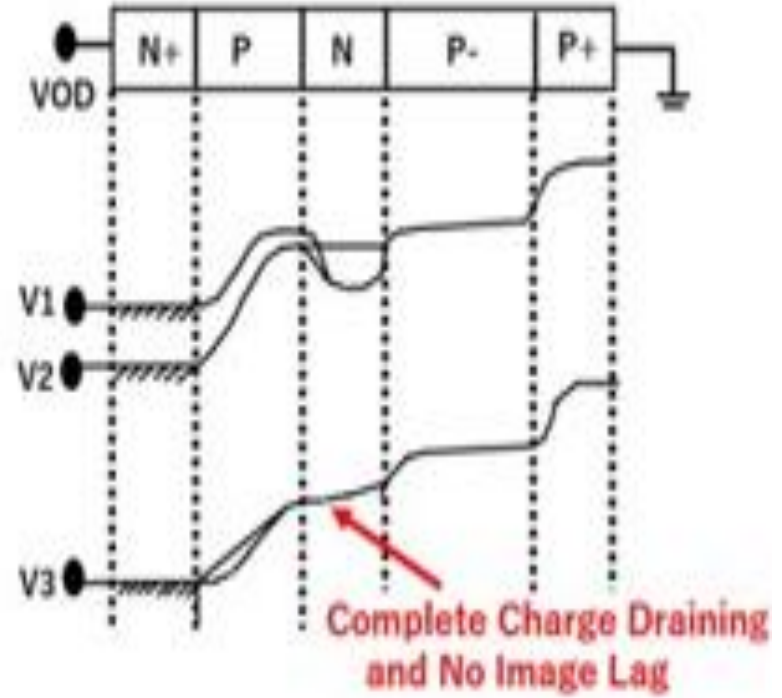
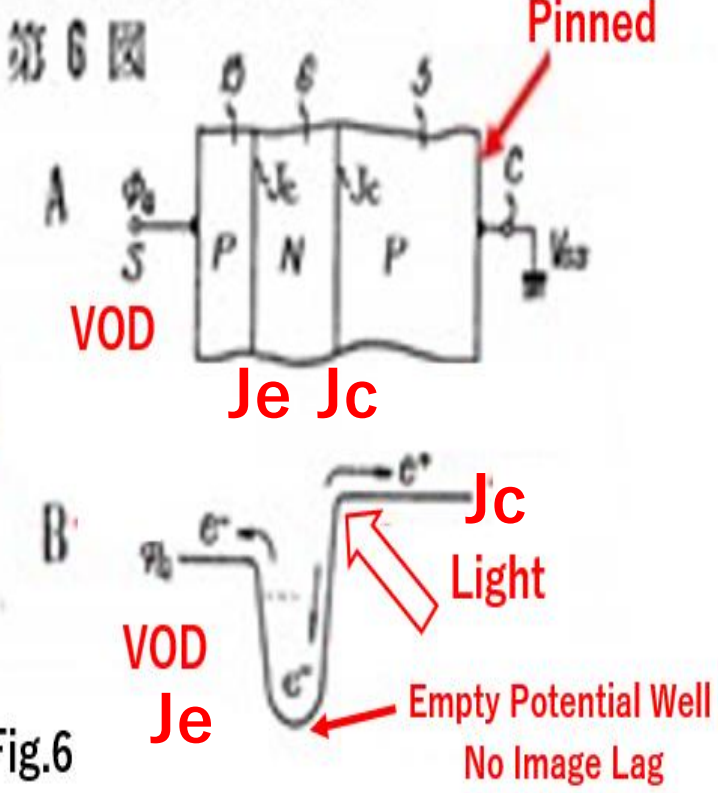


# Invention and Historical Development Efforts of Pinned Buried Photodiode.

JPA1975-127646, JPA1975-127647 and JPA1975-134986 are the evidence that Yoshiaki Hagiwara at Sony is the inventor of Pinned Buried Photodiode and the SSDM1978 paper by Hagiwara team in Sony is the evidence that Hagiwara developed the first Pinned Buried Photodiode with the no-image-lag feature, the low surface dark current and the excellent short-wave blue-light sensitivity.

JPA1975-134985



JPA1975-134985 with In-Pixel Vertical Overflow Drain (VOD)

JPA1975-134985

PNP Double Junction Dynamic Photo Transistor type Pinned Surface Buried Storage Photodiode
No Image Lag Problem
No Surface Dark Current Noise
Excellent Short-Wave Light Sensitivity